

## Foreword

In 2009 the International Conference on Defects — Recognition, Imaging, and Physics in Semiconductors (DRIP) returned to the USA after fourteen years. The XIII edition of the biannual conference was held in Oglebay, West Virginia between September 13th and 17th. The intimate and workshop-like atmosphere of the DRIP series attracted over 100 academic and industrial experts on defects in semiconductors from around the world.

This special issue includes a selection of papers presented in eleven oral and one poster session. Contributions cover a wide range of semiconductor materials, from narrow to wide band gap and from well-known silicon to emerging organic semiconductors. The common theme, in the tradition of DRIP, was always defect recognition and visualization, from point defects up to macroscopic imperfections in full wafers and devices.

The Organizing Committee would like to thank the following organizations for their sponsorship: FEI, Semilab, Quantum Focus, Office of Naval Research, Air Force Office of Scientific Research, and Army Research Office. Special thanks go to TMS for providing logistical support for the Conference.

The publication of the proceedings was made possible only through the collective effort of all the authors, reviewers, and journal staff members, and we thank them all for their invaluable contributions. We especially thank Professor Suzanne Mohny, the editor of JEM, for her assistance with the review and publication process.

The next conference, DRIP XIV, will go back to Japan and will be organized by Prof. Sekiguchi Takashi and Prof. Kenji Yoshino together with the University of Miyazaki in the fall of 2011.

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